



FUKUCOM COMPANY LTD.

福靈有限公司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

BC846W...BC850W

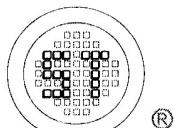
NPN Silicon Epitaxial Planar Transistor
for general purpose and switching applications



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	80	V
		50	
		30	
		30	
		50	
Collector Emitter Voltage	V_{CEO}	65	V
		45	
		30	
		30	
		45	
Emitter Base Voltage	V_{EBO}	6	V
		6	
		5	
		5	
		5	
Collector Current	I_C	100	mA
Peak Collector Current	I_{CM}	200	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$



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Dated : 21/06/2006



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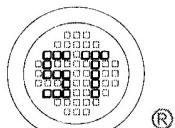
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Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 5 \text{ V}$, $I_C = 2 \text{ mA}$	h_{FE}	110	220	-
	h_{FE}	200	450	-
	h_{FE}	420	800	-
Collector Base Voltage at $I_C = 10 \mu\text{A}$	V_{CBO}	80	-	V
		50	-	
		30	-	
		30	-	
		50	-	
Collector Emitter Voltage at $I_C = 10 \text{ mA}$	V_{CEO}	65	-	V
		45	-	
		30	-	
		30	-	
		45	-	
Emitter Base Voltage at $I_E = 1 \mu\text{A}$	V_{EBO}	6	-	V
		6	-	
		5	-	
		5	-	
		5	-	
Collector Base Cutoff Current at $V_{CB} = 30 \text{ V}$	I_{CBO}	-	15	nA
Emitter Base Cutoff Current at $V_{EB} = 5 \text{ V}$	I_{EBO}	-	100	nA
Collector Emitter Saturation Voltage at $I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$ $I_C = 100 \text{ mA}$, $I_B = 5 \text{ mA}$	$V_{CE(\text{sat})}$	-	0.25 0.6	V
Base Emitter Voltage at $V_{CE} = 5 \text{ V}$, $I_C = 2 \text{ mA}$ $V_{CE} = 5 \text{ V}$, $I_C = 10 \text{ mA}$	V_{BE}	0.58 -	0.7 0.77	V
Transition Frequency at $V_{CE} = 5 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 100 \text{ MHz}$	f_T	100	-	MHz
Collector Output Capacitance at $V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$	C_{ob}	-	4.5	pF



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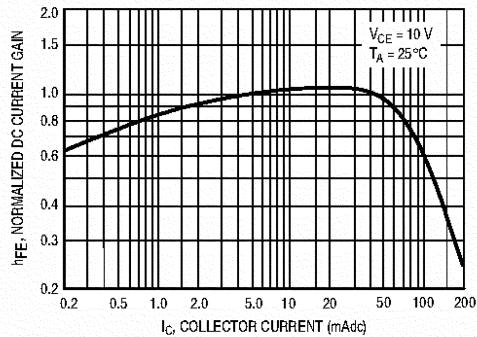


Figure 1. Normalized DC Current Gain

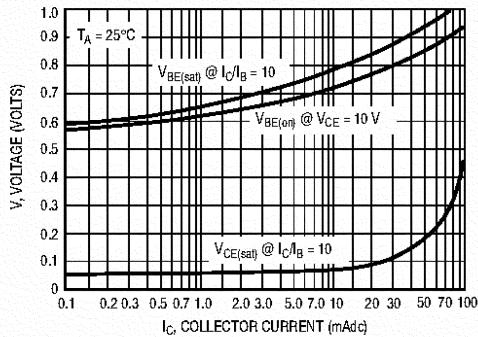


Figure 2. "Saturation" and "On" Voltages

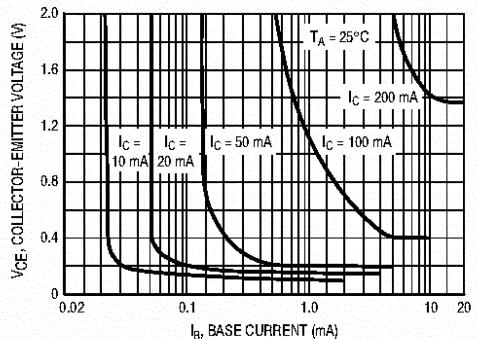


Figure 3. Collector Saturation Region

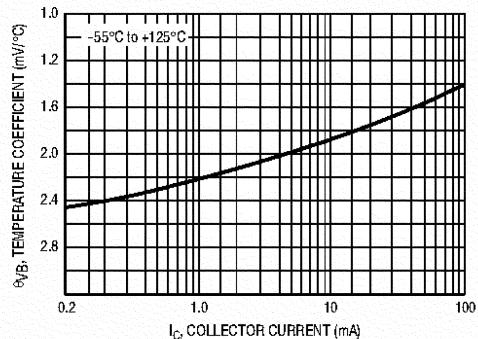


Figure 4. Base-Emitter Temperature Coefficient

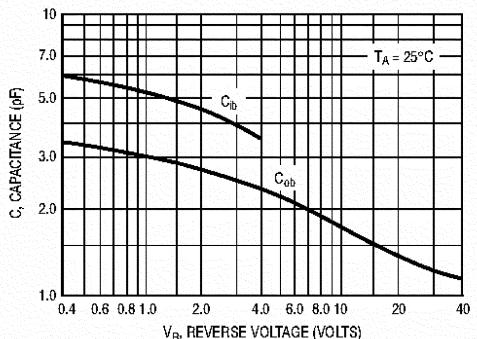


Figure 5. Capacitances

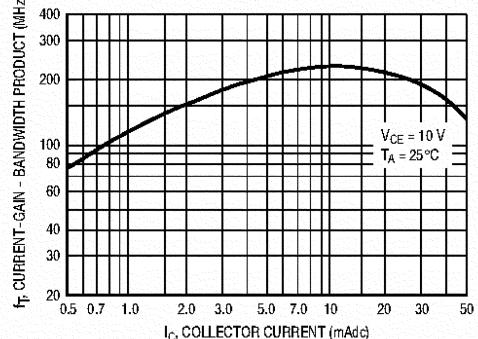
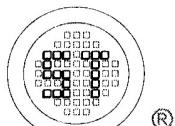


Figure 6. Current-Gain - Bandwidth Product



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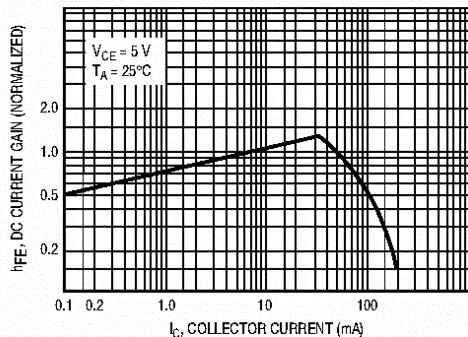


Figure 7. DC Current Gain

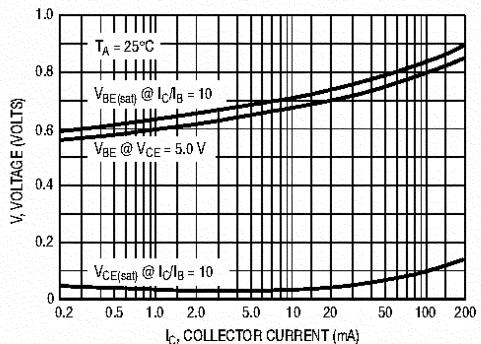


Figure 8. "On" Voltage

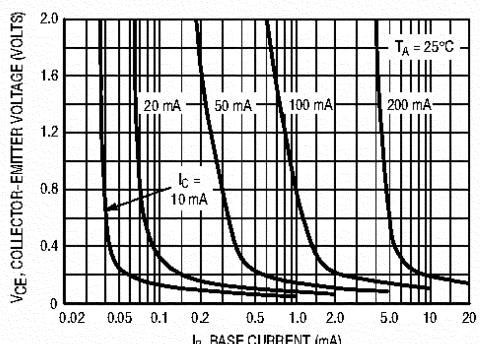


Figure 9. Collector Saturation Region

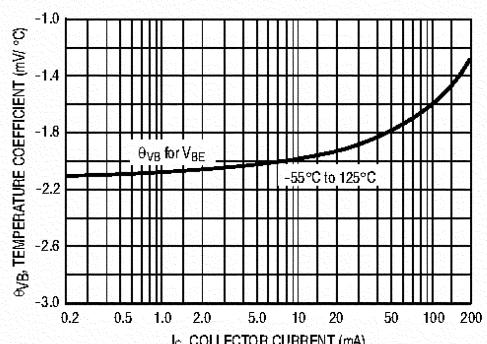


Figure 10. Base-Emitter Temperature Coefficient

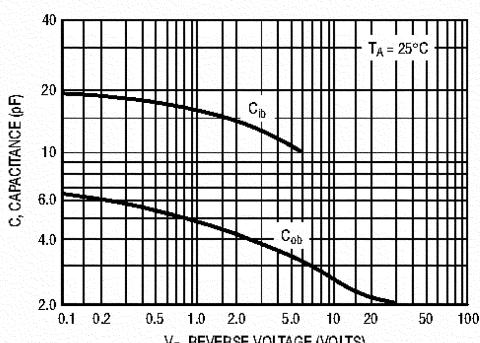


Figure 11. Capacitance

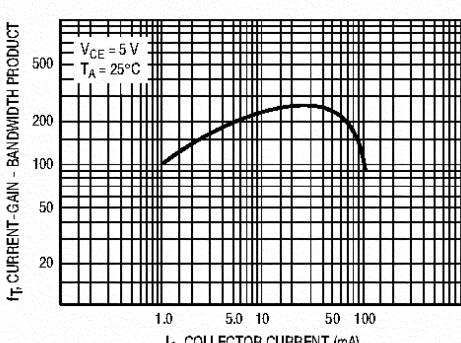
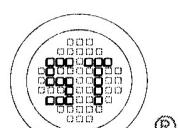


Figure 12. Current-Gain - Bandwidth Product



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